RoHS

HALOGEN

FREE

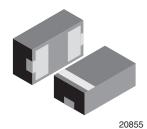
<u>GREEN</u>

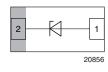
(5-2008)



Vishay Semiconductors

ESD Protection Diode in LLP1006-2L





MARKING (example only)

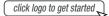


Bar = cathode marking

X = date code

Y = type code (see table below)

DESIGN SUPPORT TOOLS





FEATURES

- Ultra compact LLP1006-2L package
- Low package height < 0.4 mm
- 1-line ESD protection
- Low leakage current < 0.01 μA
- Low load capacitance C_D = 22.5 pF (V_R = 6 V; f = 1 MHz)
- ESD immunity acc. IEC 61000-4-2
 ± 30 kV contact discharge
 + 30 kV air discharge
- ± 30 kV air discharge
 High surge current acc. IEC 61000-4-5 I_{PP} > 8 A
- Soldering can be checked by standard vision inspection.
 No X-ray necessary
- Pin plating NiPdAu (e4) no whisker growth
- e4 precious metal (e.g. Ag, Au, NiPd, NiPdAu) (no Sn)
- PATENT(S): www.vishay.com/patents
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

ORDERING INFORMATION					
DEVICE NAME	CE NAME ORDERING CODE		MINIMUM ORDER QUANTITY		
VESD12A1A-HD1	VESD12A1A-HD1-GS08	8000	8000		

PACKAGE DATA						
DEVICE NAME	NAME		MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS	
VESD12A1A-HD1	LLP1006-2L	К	0.72 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C

ABSOLUTE MAXIMUM RATINGS VESD12A1A-HD1					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Peak pulse current	Acc. IEC 61000-4-5; $t_P = 8/20 \mu s$; single shot	I _{PPM}	8	Α	
Peak pulse power	Acc. IEC 61000-4-5; t _P = 8/20 μs; single shot	P_{PP}	200	W	
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V_{ESD}	± 30	kV	
	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV	
Operating temperature	Junction temperature	T_J	-40 to +125	°C	
Storage temperature		T_{stg}	-55 to +150	°C	

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and international patents.



Vishay Semiconductors

ELECTRICAL CHARACTERISTICS VESD12A1A-HD1 (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of line which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V	
Reverse voltage	At I _R = 0.1 μA	V _R	12	-	-	V	
Reverse current	At V _R = 12 V	I _R	-	< 0.01	0.1	μA	
Reverse breakdown voltage	At I _R = 1 mA	V_{BR}	13.5	14	16	V	
Reverse clamping voltage	At I _{PP} = 1 A	V _C	-	14.8	17	V	
	At I _{PP} = I _{PPM} = 8 A	V _C	-	21	24	V	
Forward clamping voltage	At I _{PP} = 0.2 A	V _F	-	0.85	1.2	V	
	At I _{PP} = 1 A	V _F	-	1.0	1.3	V	
	At I _{PP} = I _{PPM} = 8 A	V _F	-	2.0	2.5	V	
Capacitance	At V _R = 0 V; f = 1 MHz	C _D	-	54	65	pF	
	At V _R = 6 V; f = 1 MHz	C _D	-	22.5	-	pF	

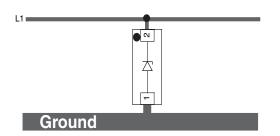
BIAs-MODE (bidirectional asymmetrical protection mode)

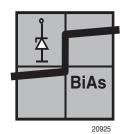
With the VESD12A1A-HD1 one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between data line and ground offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the VESD12A1A-HD1 clamping behaviour is bidirectional and asymmetrical (BiAs).





Vishay Semiconductors

TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

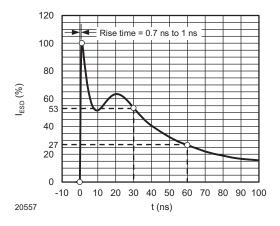


Fig. 1 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω /150 pF)

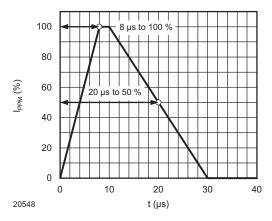


Fig. 2 - 8/20 µs Peak Pulse Current Wave Form acc. IEC 61000-4-5

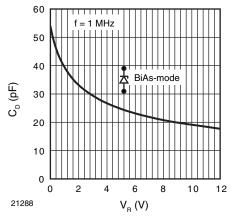


Fig. 3 - Typical Capacitance C_D vs. Reverse Voltage V_R

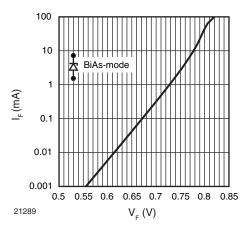


Fig. 4 - Typical Forward Current I_F vs. Forward Voltage V_F

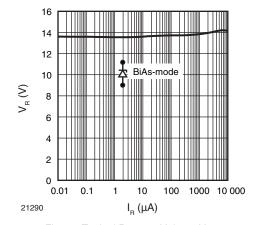


Fig. 5 - Typical Reverse Voltage V_R vs. Reverse Current I_R

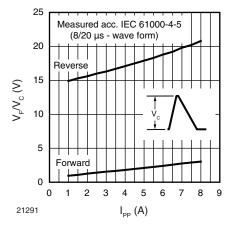


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current I_{PP}



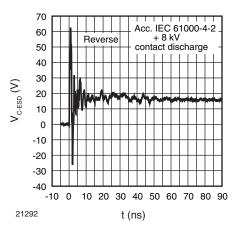


Fig. 7 - Typical Clamping Performance at + 8 kV Contact Discharge (acc. IEC 61000-4-2)

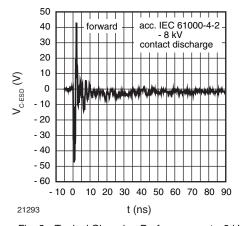


Fig. 8 - Typical Clamping Performance at - 8 kV Contact Discharge (acc. IEC 61000-4-2)

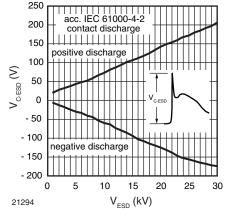
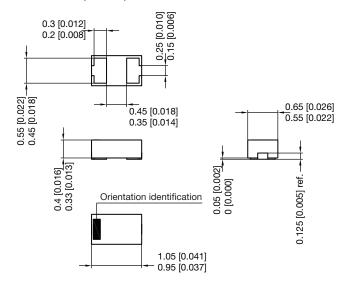


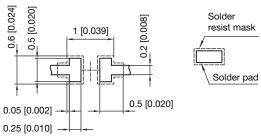
Fig. 9 - Typical Clamping Voltage at ± ESD Contact Discharge (acc. IEC 61000-4-2)

Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters (inches): LLP1006-2L



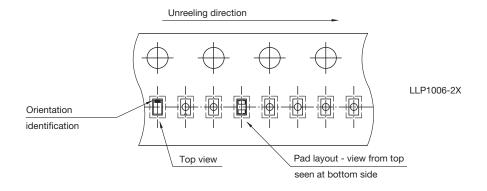
Foot print recommendation:



Pad Design Patented: (PUS 9.018.537 B2)

Document no.: S8-V-3906.04-005 (4) Rev. 7 - Date: 11.May 2016

20812



S8-V-3906.04-017 (4) 02.05.2017 22965



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.